/ Descriptions

50V~600V 2.0A SMBF

Surface Mount Superfast Recovery Rectifier,Reverse Voltage:50 to600V,Forward Current:2.0A, SMBF thin package.

/ Features

RoHS 2011/65/EU

Glass Passivated Chip Junction,Fast reverse recovery time,Lead free in comply with EU R0HS 2011/65/EU directives,For surface mounted applications,Halogen free product.

/ Applications

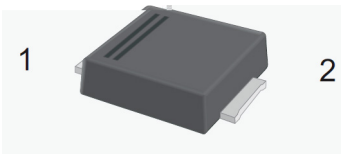
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General purpose.

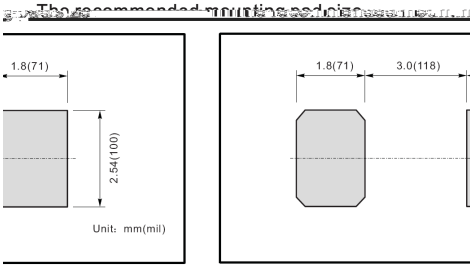
/ Equivalent Circuit



/ Pinning



PIN	DESCRIPTION
1	Cathode
2	Anode



/ Marking

See Marking Instructions.

Parameter	Symbol	Rating							Unit
		ES2ABF	ES2BBF	ES2CBF	ES2DBF	ES2EBF	ES2GBF	ES2JBF	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at T_L= 100	$I_{F\ AV}$	2.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	50							A
Typical Junction Capacitance at V_R =4V, f=1MHZ	C_j	45							pF
Typical Thermal Resistance [1]	$R_{\theta JA}$	65							/W
Operating and Storage Temperature Range	T_j,T_{stg}	-55~+150							

Note:
1 P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.

Parameter	Symbol	Test Conditions	Rating							Unit
			ES2ABF	ES2BBF	ES2CBF	ES2DBF	ES2EBF	ES2GBF	ES2JBF	
Maximum Forward Voltage	V_F	I_F=2.0A	1.0				1.25		1.65	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I_R	T_a=25	5.0							μA
		T_a=125	100							μA
Maximum Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{rr}								

/ Electrical Characteristic Curve

, M y ƒ / Marking Instructions

š WD t ... • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y			Note:
1o• Ä ½ “ †	150 ½180 - k ž •	60 ½90sec;	1.Preheating:150~180 - , Time:60~90sec.
2o• Q › “ †	245 r5 - k ž • 4 Ò	5 r	